



Hydrogen solution in tetrahedral or octahedral interstitial sites in Al

C.A. Zeng, J.P. Hu, C.Y. Ouyang*

Department of Physics, Jiangxi Normal University, Nanchang 330022, China

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ABSTRACT

It is reported that H atoms prefer to stay at interstitial (defect) sites with larger space in most metals. However, H atom prefers to occupy tetrahedral interstitial sites (T-site) that provide smaller space than octahedral sites (O-site) in Al. This paper studied the H–Al interactions from first principles calculations. Through analysis of the H-induced electronic states and the local atomic relaxations, we show that H–Al bonding interaction is stronger for T-site H, which is in favor of the solution energy. On the other hand, larger local atomic distortion is observed around the T-site H, which increases the total energy.

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1. Introduction

The interaction between hydrogen and metal is one of the most important topics in materials physics, having broad range of technological implications. The bonding of H with metals determines the H storage capacity and desorption rate of H₂ from the metal hydrides [1,2]. In the process of production of H₂ via metal catalyzed chemical reactions, the H–metal interaction plays an important role [3]. Despite many years of research, some fundamental aspects underlying the H–metal interaction remains poorly understood because of the complex nature of this interaction.

H–metal interaction is also relevant to the H embrittlement. In recent years, a number of first principles studies have investigated the H embrittlement. Lu and Kaxiras have found that vacancies play crucial role in H embrittlement of Al [4], and Liu et al. also emphasize the role of vacancies in W [5]. In both cases, it is found that H prefers locating at tetrahedral sites (T-sites). According to Liu et al., H prefers to site at T sites in body centered cubic (BCC) W because T-sites provides more space to accommodate H atom, and this interstitial space determined site preference idea applies correctly to many other BCC metals such as group V transition metals

[6]. This idea is also confirmed by other face centered cubic (FCC) metals such as Cu and Pd [7], in which H prefers to take octahedral sites (O-sites) since O-sites provides more space in FCC structures. However, this idea is not true for the case of FCC Al. In Al, although O-sites provide more spaces for H accommodation, H prefers to take T sites.

As mentioned above, the H embrittlement is always relevant to the formation of vacancies, in which H may accumulate since vacancies provide large amount of space. On the other hand, vacancy reduces charge density in its vicinity to provide an isosurface for collective H binding, causing H segregation and hence H bubble nucleation when H density reaches a critical density on the internal vacancy surface [5]. Obviously, the mechanism on the vacancy assisted H embrittlement is strongly related with the assumption that H prefers to stay at places with more spaces (interstitials sites or vacancies).

In the present work, we present systematic studies on H–Al interaction, we demonstrate the H occupying T-site is more stable than O-site, trying to understand the intrinsic physics concerning the “abnormal” behavior of H dissolution in FCC Al lattice.

2. Computational details

Calculations are done within the plane-wave pseudopotential method and density functional theory (DFT), which are imple-

* Corresponding author. Tel.: +86 791 8120370; fax: +86 791 8120430.

E-mail address: cyouyang@jxnu.edu.cn (C.Y. Ouyang).

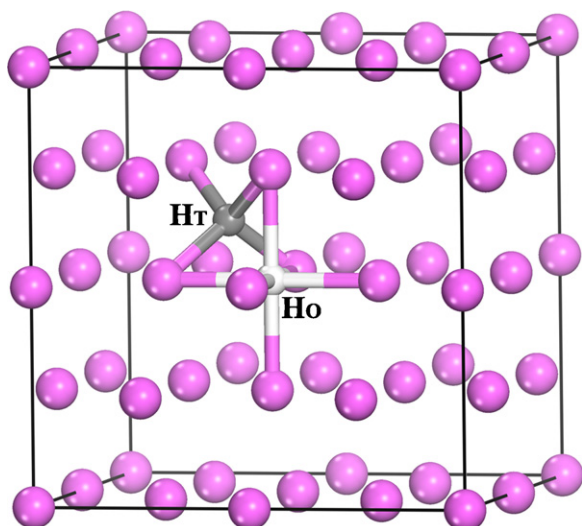


Fig. 1. Schematic view of the octahedral and tetrahedral H atoms in FCC Al. Large (purples) and small (grey for H_T and white for H_O) balls are Al and H atoms, respectively. (For interpretation of the references to color in this figure legend, the reader is referred to the web version of the article.)

mented in the Vienna ab initio simulation package (VASP) [8,9]. The core ion and valence electron interaction is described by the projector augmented-wave method (PAW) [10], while the exchange–correlation part is described with generalized gradient approximation (GGA) by Perdew and Wang [11]. The convergence tests of the total energy with respect to the K-points sampling have been carefully examined. A $2 \times 2 \times 2$ supercell is used for the Al metal system and a Monkhorst–Pack [12] scheme of $5 \times 5 \times 5$ K-point mesh is used for the K-points sampling within the Brillouin zone. Energy cut-off for the plane waves is chosen to be 300 eV. Before the calculation of the electronic structure, all the atomic positions and lattice parameters are fully relaxed and the final forces on all relaxed atoms are less than 0.005 eV/Å. The Methfessel–Paxton smearing method [13] with $N=1$ and $\sigma=0.2$ eV is used in all calculations to treat metallic systems.

3. Results and discussion

Fig. 1 shows schematically the octahedral and tetrahedral H atoms in the Al $2 \times 2 \times 2$ supercell. The optimized lattice constant of FCC Al is 4.0495 Å, which agrees well with the experimental date 4.049 Å [14]. Using this lattice constant and taking into account that atoms are closely packed along the $\langle 110 \rangle$ direction in the FCC lattice, the “radii” of the T-sites and O-sites are 0.32 Å and 0.59 Å, respectively. H_2 molecule has a covalent radius of 0.37 Å, which is slightly larger than the radii of T-sites and much small than the radii of O-sites. When we examine the details of the relaxed structures of $Al_{32}H$, we find that the cell shape remains unchanged and only the nearest neighboring (NN) Al atoms to the H atom move outwards by 0.13 Å and 0.04 Å when H is present in the T-site and O-site, respectively (refer to Table 1). The volume expansion of the supercell is *c.a.* 0.71% and 0.37% for H at T- and O-site cases, respectively. Very clearly, those data show that H atom at T-site repels

Table 1
The lattice constant a and local atomic structure of $Al_{32}H_T$ and $Al_{32}H_O$.

	Unrelaxed		Relaxed		ΔV (%)	Δd (%)
	a	d_{H-Al} (Å)	a	d_{H-Al} (Å)		
$Al_{32}H_T$	8.099	1.753	8.118	1.885	0.71	7.5
$Al_{32}H_O$	8.099	2.025	8.109	2.065	0.37	1.9

Table 2

Solution energies of H in dilute limit in different metals. The superscript “ZPE” denotes that zero point energy is included in the calculations.

	Solution energy (eV/H)		
	T interstitial site	O interstitial site	$E_{sol}(O) - E_{sol}(T)$
Al (FCC)	0.69 (0.68 ^a)	0.77 (0.77 ^a)	0.08 (0.09 ^a)
Al (BCC)	−0.02	0.38	0.40
Pd (FCC)	−0.02 ^{ZPE b}	−0.16 ^{ZPE b}	0.14 ^{ZPE b}
V (BCC)	−0.32 ^c	−0.17 ^c	0.15 ^c
Fe (BCC)	0.20 ^d	0.33 ^d	0.13 ^d

^a Ref. [15].

^b Ref. [16].

^c Ref. [6].

^d Ref. [7].

its NN Al atoms more than at O-site, indicating that NN Al atoms interact much strongly with T-site H.

The interaction of interstitial H and host metal atoms can be studied by the solution energy, which is defined as $E_{sol} = E[\text{Metal} + H] - E[\text{Metal}] - \frac{1}{2}E[H_2]$, where $E[\text{Metal} + H]$, $E[\text{Metal}]$, and $E[H_2]$ are calculated total energies of the metal with one interstitial H atom, pure metal, and H_2 molecule in vacuum, respectively. The results are summarized in Table 2, in which solution energies of other BCC and FCC metals are also presented for comparison. As it is shown in Table 2, the tetrahedral interstitial site in FCC Al is slightly more favorable than the octahedral interstitial site by 0.08 eV. For all other cases listed in Table 2, H prefers to take T-sites in BCC lattice while O-sites in FCC lattice. As far as we know, for any other metals that we did not listed in Table 2, the H site preference is the same. Based on this point, we may think it could be interesting to know the site preference in the unstable BCC Al. Therefore, we calculate the solution energies and we found that H prefers to take T-site in BCC Al. The lattice constant of the BCC structure is chosen to be 3.214 Å, with which the mass density of the BCC Al is the same as the FCC Al. Then, if we take into account that Al atoms are closely packed along the $\langle 111 \rangle$ direction in the BCC structure, the radii of the T-site and O-site in BCC Al are 0.41 and 0.22 Å respectively. The space of T-site in BCC Al is large than that of FCC Al (0.32 Å) while the space of O-site in BCC Al is much small than FCC Al (0.59 Å). The calculated solution energies are −0.02 and 0.38 eV/H for T-sites and O-sites in BCC Al.

Now we discuss the electronic structure of Al–H system. Fig. 2 is the orbital projected density of states (PDOS) to Al atoms in $Al_{32}H_T$ and $Al_{32}H_O$. As it can be seen from Fig. 2, major differences are peaks at around −11.5 to −10.5 eV below the Fermi level. This difference is contributed by the so called H-induced states in the system. Because of the H–Al interaction, the Al-states (3p or 3s) at lowest energy ranges will form bonding and anti-bonding states with H-1s states. The bonding states will become lower in energy, and when the intensity of the interaction is stronger, the energy level of the bonding state is lower. In this sense, interstitials H in metal lattice pulls down part of the occupied metal states. As it is shown in Fig. 2(b) and c, the Al-3s and 3p states are pulled down by the H atom in both $Al_{32}H_T$ and $Al_{32}H_O$ cases, and the H-induced states are a little bit lower in energy level in the case of $Al_{32}H_T$, indicating that the H–Al interaction is a little bit more strong in $Al_{32}H_T$. We mention here that the PDOS of Al atoms far away from H atom in

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